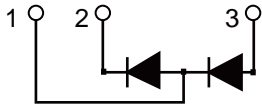


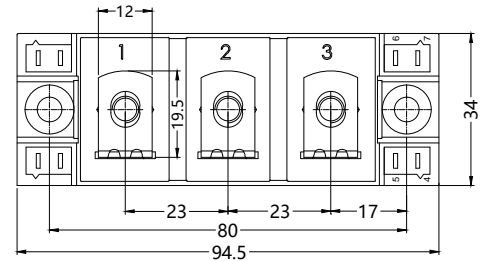
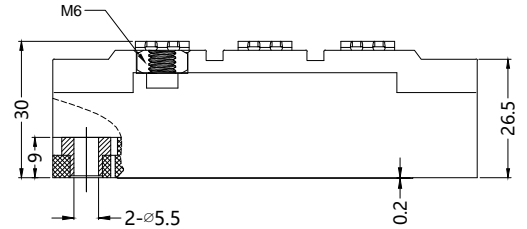
SDD190N18

Diode-Diode Modules



Type	V _{RSM} V	V _{RRM} V
SDD190N08	900	800
SDD190N12	1300	1200
SDD190N14	1500	1400
SDD190N16	1700	1600
SDD190N18	1900	1800

Dimensions in mm (1mm=0.0394")



Symbol	Test Conditions	Maximum Ratings	Unit
I _{FRMS} I _{FAVM}	T _{VJ} =T _{VJM} T _C =100°C; 180° sine	300 190	A
I _{FSM}	T _{VJ} =45°C sine V _R =0 t=10ms (50Hz), t=8.3ms (60Hz), sine	6600 7290	A
	T _{VJ} =T _{VJM} V _R =0 t=10ms(50Hz), sine t=8.3ms(60Hz), sine	5600 6200	
∫i ² dt	T _{VJ} =45°C sine V _R =0 t=10ms (50Hz), t=8.3ms (60Hz), sine	218000 221000	A ² s
	T _{VJ} =T _{VJM} V _R =0 t=10ms(50Hz), sine t=8.3ms(60Hz), sine	157000 160000	
T _{VJ} T _{VJM} T _{stg}		-40...+150 150 -40...+125	°C
V _{ISOL}	50/60Hz, RMS I _{ISOL} ≤1mA t=1min t=1s	3000 3600	V~
M _d	Mounting torque (M6) Terminal connection torque (M6)	2.25-2.75/20-25 4.5-5.5/40-48	Nm/lb.in.
Weight	Typical	118	g



Sirectifier[®]

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Diode-Diode Modules

Symbol	Test Conditions	Characteristic Values	Unit
I_R	$T_{VJ}=T_{VJM}; V_R=V_{RRM}$	20	mA
V_F	$I_F=300A; T_{VJ}=25^{\circ}C$	1.15	V
V_{TO}	For power-loss calculations only	0.8	V
r_T	$T_{VJ}=T_{VJM}$	0.8	m Ω
Q_s	$T_{VJ}=125^{\circ}C; I_F=300A; -di/dt=50A/us$	550	μC
I_{RM}		235	A
R_{thJC}	per diode; DC current per module	0.21 0.105	K/W
R_{thJK}	per diode; DC current per module	0.31 0.155	K/W
d_s	Creepage distance on surface	12.7	mm
d_A	Strike distance through air	9.6	mm
a	Maximum allowable acceleration	50	m/s ²

FEATURES

- * International standard package
- * DCB Base plate
- * Glass passivated chips
- * Isolation voltage 3600 V~
- * UL File NO.E310749
- * RoHS Compliance

APPLICATIONS

- * Supplies for DC power equipment
- * DC supply for PWM inverter
- * Field supply for DC motors
- * Battery DC power supplies

ADVANTAGES

- * Space and weight savings
- * Simple mounting
- * Improved temperature and power cycling
- * Reduced protection circuits

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Diode-Diode Modules

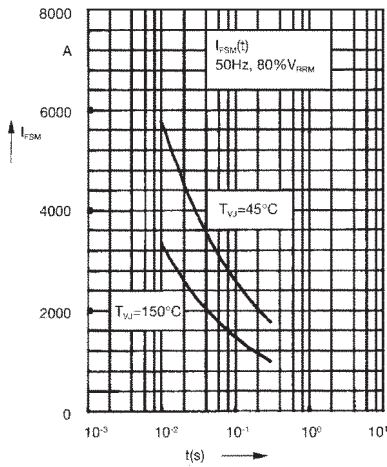


Fig. 1 Surge overload current
 I_{FSM} : Crest value, t : duration

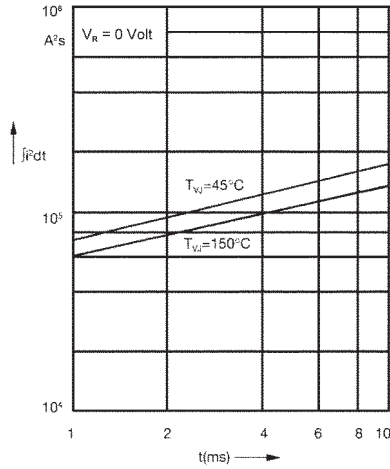


Fig. 2 $\int i^2 dt$ versus time (1-10 ms)

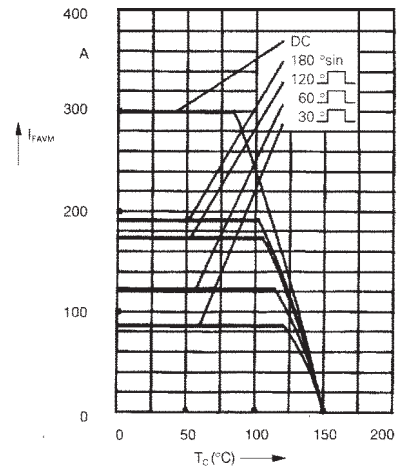


Fig. 2a Maximum forward current at case temperature

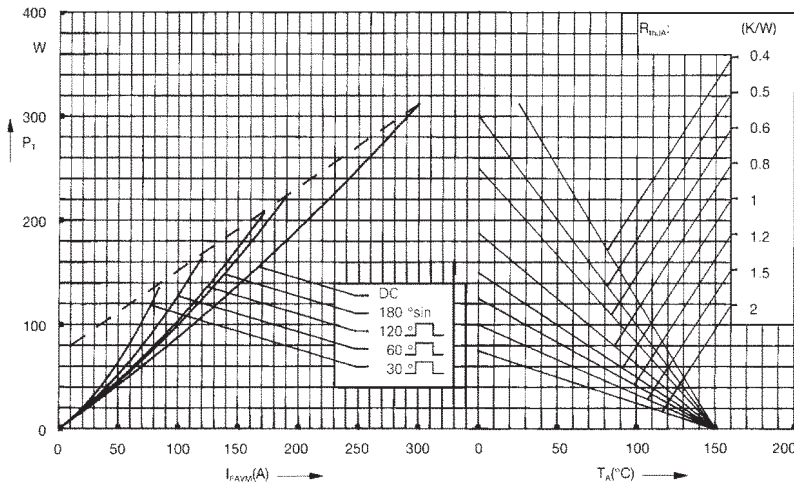


Fig. 3 Power dissipation versus forward current and ambient temperature (per diode)

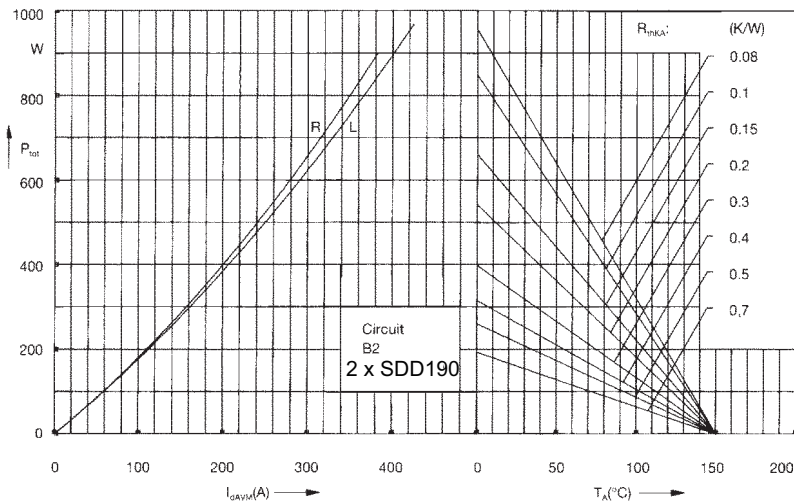


Fig. 4 Single phase rectifier bridge:
 Power dissipation versus direct output current and ambient temperature
 R = resistive load
 L = inductive load

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Diode-Diode Modules

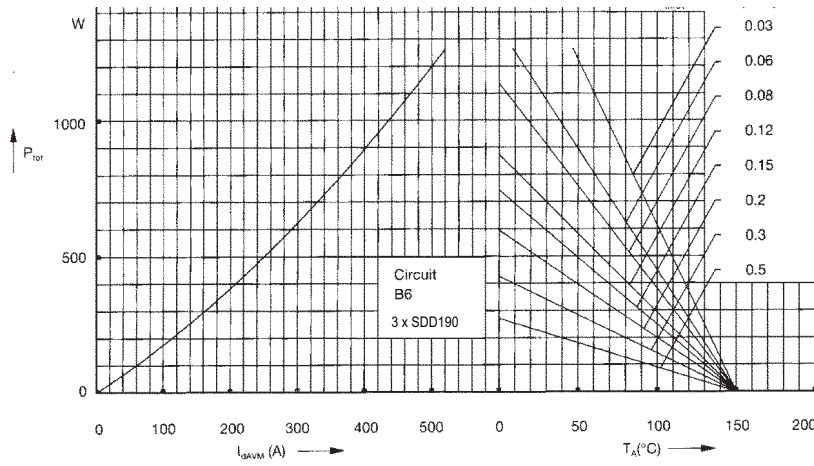


Fig. 5 Three phase rectifier bridge: Power dissipation versus direct output current and ambient temperature

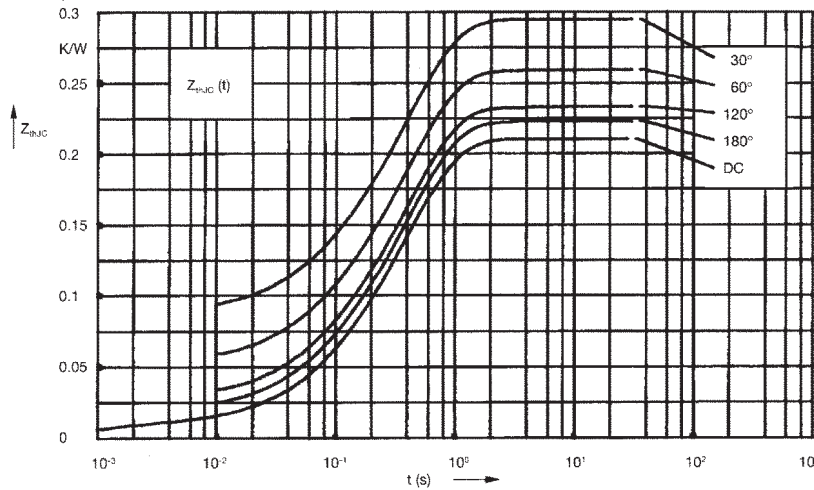


Fig. 6 Transient thermal impedance junction to case (per diode)

R_{thJC} for various conduction angles d:

d	R_{thJC} (K/W)
DC	0.210
180°C	0.223
120°C	0.233
60°C	0.260
30°C	0.295

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.0087	0.001
2	0.0163	0.065
3	0.185	0.4

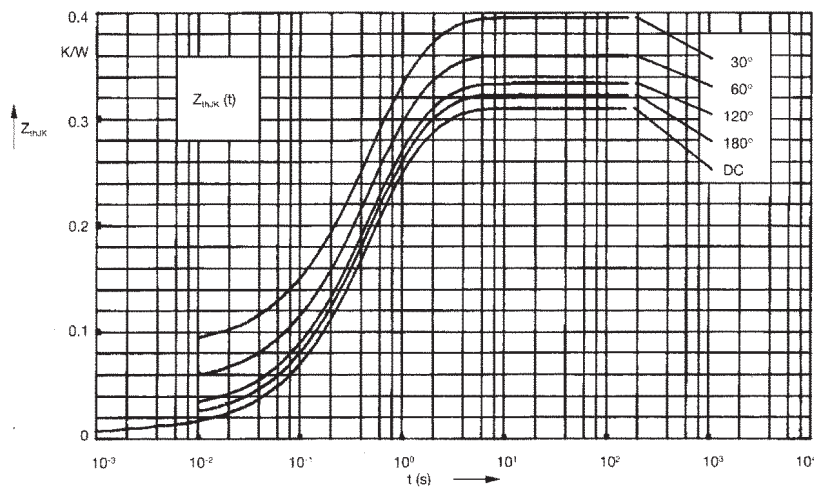


Fig. 7 Transient thermal impedance junction to heatsink (per diode)

R_{thJK} for various conduction angles d:

d	R_{thJK} (K/W)
DC	0.31
180°C	0.323
120°C	0.333
60°C	0.360
30°C	0.395

Constants for Z_{thJK} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.0087	0.001
2	0.0163	0.065
3	0.185	0.4
4	0.1	1.29